Zexuan Zhang

List of Publications by Citations

11 papers	235 citations	5 h-index	11 g-index
11 ext. papers	293 ext. citations	3 avg, IF	2.8 L-index

#	Paper	IF	Citations
11	Breakdown mechanism in 1 kA/cm2 and 960 V E-mode Ga2O3 vertical transistors. *Applied Physics Letters*, **2018**, 113, 122103	3.4	91
10	1230 V Ga2O3 trench Schottky barrier diodes with an ultra-low leakage current of . *Applied Physics Letters*, **2018**, 113, 202101	3.4	61
9	The new nitrides: layered, ferroelectric, magnetic, metallic and superconducting nitrides to boost the GaN photonics and electronics eco-system. *Japanese Journal of Applied Physics*, **2019**, 58, SC0801	1.4	43
8	2.44 kV Ga2O3 vertical trench Schottky barrier diodes with very low reverse leakage current **2018**,		23
7	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. *Applied Physics Letters*, **2021**, 119, 162104	3.4	6
6	Spin Orbit torque field-effect transistor (SOTFET): Proposal for a magnetoelectric memory. *Applied Physics Letters*, **2020**, 116, 242405	3.4	4
5	Magnetic properties of MBE grown Mn4N on MgO, SiC, GaN and Al2O3 substrates. *AIP Advances*, **2020**, 10, 015238	1.5	3
4	Very High Density (>10 14 cm) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. *Advanced Electronic Materials*,2101120	6.4	3
3	Materials Relevant to Realizing a Field-Effect Transistor Based on Spin Orbit Torques. *IEEE Journal on Exploratory Solid-State Computational Devices and Circuits*, **2019**, 5, 158-165	2.4	1
2	Epitaxial Ferrimagnetic Mn4N Thin Films on GaN by Molecular Beam Epitaxy. *IEEE Transactions on Magnetics*, **2021**, 1-1	2	0
1	Distributed polarization-doped GaN p diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. *Applied Physics Letters*, **2022**, 120, 122111	3.4	0